N-Channel Depletion-Mode DMOS FET

Features

► Free from secondary breakdown
► Low power drive requirement
► Ease of paralleling
► Excellent thermal stability
► Integral source-drain diode
► High input impedance and low C_{ISS}
► ESD gate protection

Applications

► Solid state relays
► Normally-on switches
► Converters
► Power supply circuits
► Constant current sources
► Input protection circuits

General Description

The LND250 is a high voltage N-channel depletion mode (normally-on) transistor utilizing Supertex's lateral DMOS technology. The gate is ESD protected.

The LND250 is ideal for high voltage applications in the areas of normally-on switches, precision constant current sources, voltage ramp generation and amplification.

Ordering Information

Part Number	Package Options	Packing
LND250K1-G*	TO-236AB (SOT-23)	3000/Reel

-G denotes a lead (Pb)-free / RoHS compliant package
* Part is not recommended for new designs. Please refer to LND150K1-G.

Product Summary

BV_{DSX}/BV_{DGX} (V)	$R_{DS(ON)}$ (max)	I_{DSS} (min)
500	1.0kΩ	1.0mA

Absolute Maximum Ratings

Parameter	Value
Drain-to-source	BV_{DSX}
Drain-to-gate	BV_{DGX}
Gate-to-source	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration

SOURCE
DRAIN
GATE

TO-236AB (SOT-23)

Product Marking

NDEW

W = Code for Week Sealed
——— = "Green" Packaging

TO-236AB (SOT-23)

Packages may or may not include the following marks: Si or

Thermal Characteristics

Package	I_D (continuous)[†] (mA)	I_D (pulsed) (mA)	Power Dissipation @T_A = 25°C (W)	θ_{ja} (°C/W)	I_{DR} (mA)	I_{DRM}[†] (mA)
TO-236AB (SOT-23)	13	30	0.36	203	13	30

Notes:
† I_D (continuous) is limited by max rated T_j.

Electrical Characteristics *(T_A = 25°C unless otherwise specified)*

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSX}	Drain-to-source breakdown voltage	500	-	-	V	V_{GS} = -10V, I_D = 1.0mA
$V_{GS(OFF)}$	Gate-to-source off voltage	-1.0	-	-3.0	V	V_{GS} = 25V, I_D = 100nA
$\Delta V_{GS(OFF)}$	Change in $V_{GS(OFF)}$ with temperature	-	-	5.0	mV/°C	V_{GS} = 25V, I_D = 100nA
I_{GSS}	Gate body leakage current	-	-	100	nA	V_{GS} = ± 20V, V_{DS} = 0V
$I_{D(OFF)}$	Drain-to-source leakage current	-	-	100	nA	V_{GS} = -10V, V_{DS} = 450V
		-	-	100	µA	V_{DS} = 0.8V Max Rating, V_{GS} = -10V, T_A = 125°C
I_{DSS}	Saturated drain-to-source current	1.0	-	3.0	mA	V_{GS} = 0V, V_{DS} = 25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	850	1000	Ω	V_{GS} = 0V, I_D = 0.5mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.2	%/°C	V_{GS} = 0V, I_D = 0.5mA
G_{FS}	Forward transductance	1.0	2.0	-	mmho	V_{DS} = 0V, I_D = 1.0mA
C_{ISS}	Input capacitance	-	7.5	10	pF	V_{GS} = -10V, V_{DS} = 25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	2.0	3.5		
C_{RSS}	Reverse transfer capacitance	-	0.5	1.0		
$t_{d(ON)}$	Turn-on delay time	-	0.09	-	µs	V_{DD} = 25V, I_D = 1.0mA, R_{GEN} = 25Ω
t_r	Rise time	-	0.45	-		
$t_{d(OFF)}$	Turn-off delay time	-	0.1	-		
t_f	Fall time	-	1.3	-		
V_{SD}	Diode forward voltage drop	-	-	0.9	V	V_{GS} = -10V, I_{SD} = 1.0mA
t_{rr}	Reverse recovery time	-	200	-	ns	V_{GS} = -10V, I_{SD} = 1.0mA

Notes:
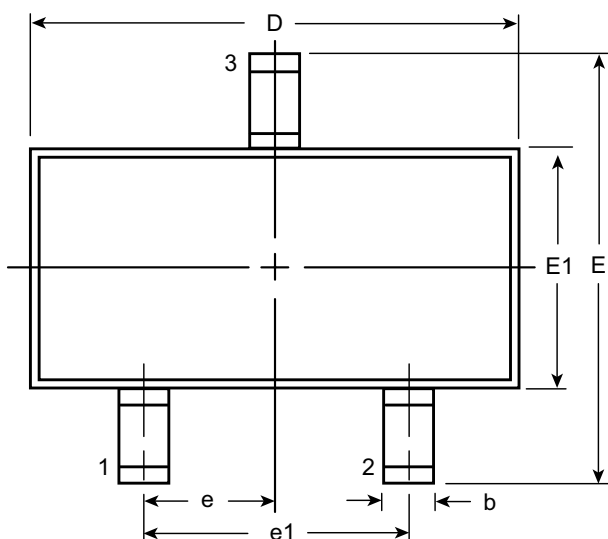1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.
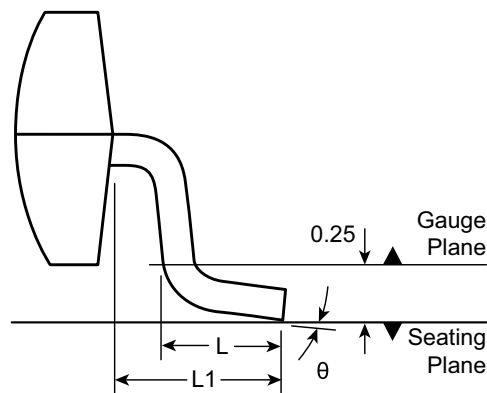
Switching Waveforms and Test Circuit
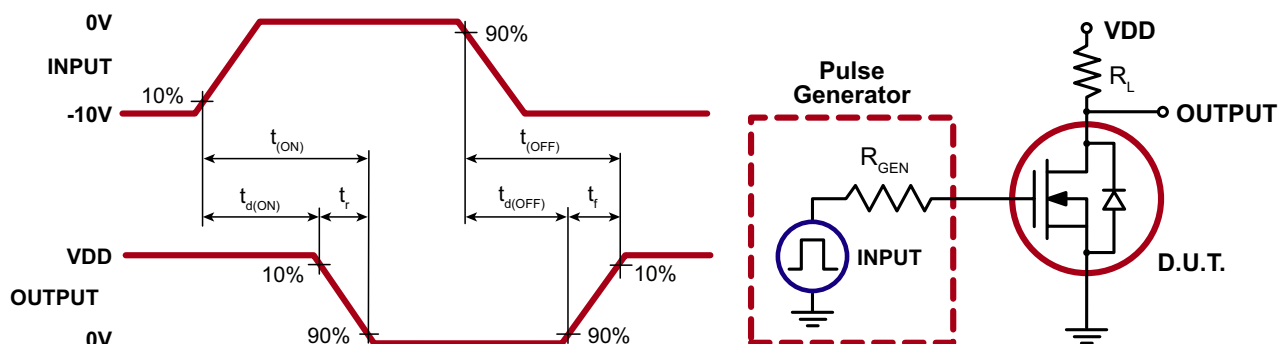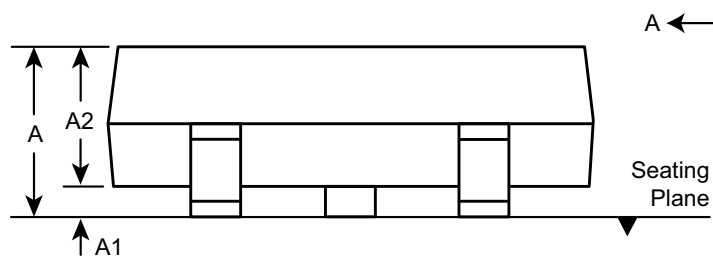
3-Lead TO-236AB (SOT-23) Package Outline (K1)
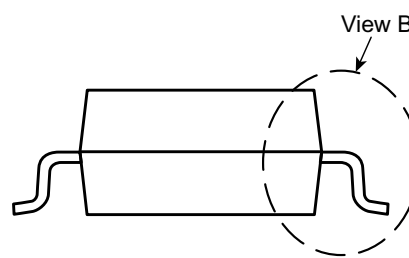## *2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch*

Top View

View B

Side View

View A - A

Symbol		A	A1	A2	b	D	E	E1	e	e1	L	L1	θ
Dimension (mm)	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.95 BSC	1.90 BSC	0.20†	0.54 REF	0°
	NOM	-	-	0.95	-	2.90	-	1.30			0.50		-
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40			0.60		8°

JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.
† This dimension differs from the JEDEC drawing.
Drawings not to scale.
Supertex Doc.#: *DSPD-3TO236ABK1, Version C041309.*

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

Supertex inc.

1235 Bordeaux Drive, Sunnyvale, CA 94089
Tel: 408-222-8888
www.supertex.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET *category:*

Click to view products by Microchip *manufacturer:*

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3 2SK2614(TE16L1,Q)